

PATENT  
740756 1986

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



in re PATENT application of:

Yasuhiko TAKEMURA

Application No.: 09/342,235

Filed: June 29, 1999

For: SEMICONDUCTOR DEVICE HAVING AT  
LEAST FIRST AND SECOND THIN FILM  
TRANSISTORS (As Amended)

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) Art Unit: 2826

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) Examiner: A. SEFER  
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AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

January 9, 2002  
(Wednesday)  
*11/24/02*  
*Amend*  
*11/24/02*

Dear Sir:

In response to the Examiner's non-Final Office Action mailed August 9, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 9 and 11 to read as follows:

9. (Amended) A semiconductor device comprising:
- a substrate having an insulating surface;
  - at least first and second semiconductor islands formed over said substrate wherein each of the semiconductor islands has a channel region and a pair of impurity regions;
  - an insulating film formed over said substrate, said insulating film including at least first and second gate insulating films formed over said first and second semiconductor islands, respectively;